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(54) THIN FILM TRANSISTOR-LIQUID CRYSTAL DISPLAY AND FABRICATING METHOD THEREOF

(57) Abstract:

PURPOSE: A thin film transistor-liquid crystal display and its fabricating method thereof are provided to prevent opening of a data line due to a step at the lower layer of the data line without any additional process by forming a data line redundancy layer with the same material as that of a pixel electrode.

CONSTITUTION: A gate electrode (10a) and a gate line are formed on a glass substrate (100). An anodized film (12) is formed to cover the gate electrode (10a). A gate insulation film (14) is formed to cover the anodized film 12 and the gate line. A semiconductor pattern (16) is formed on the gate insulation film (14) at the upper portion of the gate electrode (10a). A source electrode (20a) and a drain electrode (20b) are formed on the semiconductor pattern (16). A data line (20) is formed to be connected with the source electrode (20a) on the gate insulation film (14) at the upper portion of the gate line and crosses the gate line. A protective film (22) is inserted to be connected with the drain electrode (20b) to thereby form a pixel electrode (25). The protective film (22) is inserted to be connected with the data line (20) at the portion where the gate line and the data line (20) are crossed, to thereby form a data line redundancy layer (25').

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